

L Number	Hits	Search Text	DB	Time stamp
11	79004	ozone	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/19 15:05
12	263967	oxidize or oxidizing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/19 15:06
13	9070	ozone same (oxidize or oxidizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/19 15:06
14	960	ozone near (oxidize or oxidizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/19 15:07
15	1380328	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/19 15:07
16	35	(ozone near (oxidize or oxidizing)) same semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/19 15:08
-	6009	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:12
-	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and metallic and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:40
-	0	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) with metallic and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:16
-	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or (metal\$4 adj clusters)) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:18

-	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:20
-	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:22
-	3	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:25
-	647766	(metallic or(metal\$4 adj (cluster\$1 or element\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:58
-	0	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:48
-	0	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2 adj element) and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:30
-	23348	((second and first and third) adj (semiconductor (film\$1 or layer\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:34
-	0	((metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1)))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:37
-	3	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) and ((second and first) adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:39
-	1	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and metallic and ((second and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)) and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:41

-	15096	getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:26
-	2810	((metallic or(metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:43
-	12	((metallic or(metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:44
-	0	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and ((second and first and third) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:52
-	0	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and ((first and second and third) adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:54
-	5	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and (first adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:27
-	9	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and (semiconductor adj (film\$1 or layer\$1)) and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 18:56
-	8595	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:28
-	0	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:31
-	1086	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:32
-	715	((metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous) and crystall\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:32
-	189	((metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous) and crystall\$4) and inert adj gas\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:33
-	14	((metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and amorphous) and crystall\$4) and inert adj gas\$2) and (barrier adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 20:33
-	6	((("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or ("6107639"))).PN.	USPAT; US-PGPUB	2002/06/07 13:54

-	4	((("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or ("6107639")).PN.) and barrier	USPAT; US-PGPUB	2002/06/07 14:52
-	3	(((((("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or ("6107639")).PN.) and barrier) and block\$3	USPAT; US-PGPUB	2002/06/07 14:51
-	1	((("6396147").PN.) and barrier	USPAT; US-PGPUB	2002/06/07 14:53
-	1	((("6396147").PN.) and barrier) and amorphous	USPAT; US-PGPUB	2002/06/07 14:53
-	1	(((((("6396147").PN.) and barrier) and amorphous) and crystal\$4	USPAT; US-PGPUB	2002/06/07 14:53
-	1	((((((("6396147").PN.) and barrier) and amorphous) and crystal\$4) and inert adj gas	USPAT; US-PGPUB	2002/06/07 14:54
-	1	((((((("6396147").PN.) and barrier) and amorphous) and crystal\$4) and inert adj gas) and getter\$3	USPAT; US-PGPUB	2002/06/07 14:54
-	835	((438/166) or (438/486) or (438/476)).CCLS.	USPAT; US-PGPUB	2002/06/08 13:58
-	215	((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3	USPAT; US-PGPUB	2002/06/08 14:43
-	28	(((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and (inert or noble) adj gas	USPAT; US-PGPUB	2002/06/08 14:43
-	9	((((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and (inert or noble) adj gas) and barrier	USPAT; US-PGPUB	2002/06/08 14:44
-	0	("FOR0146").PN.	USPAT; US-PGPUB	2002/06/08 14:08
-	0	("FOR0146").PN.	JPO; DERWENT; IBM_TDB	2002/06/10 19:02
-	96	(((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and amorphous	USPAT; US-PGPUB	2002/06/08 14:43
-	16	((((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and amorphous) and (inert or noble) adj gas	USPAT; US-PGPUB	2002/06/08 14:43
-	6	((((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and amorphous) and (inert or noble) adj gas) and barrier	USPAT; US-PGPUB	2002/06/08 14:44
-	1	("6396147").PN.	USPAT; US-PGPUB	2002/06/10 17:37
-	1	("5789284").PN.	USPAT; US-PGPUB	2002/06/10 17:37
-	0	("FOR 146").PN.	JPO; DERWENT; IBM_TDB	2002/06/10 19:04
-	9	(metallic or(metal\$4 adj (cluster\$1 or element\$1))) with (anneal\$ with (electric adj current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/21 16:53
-	1	("20020086469").PN.	USPAT; US-PGPUB	2003/06/02 17:02
-	19346	kim.in.	USPAT; US-PGPUB	2003/06/02 17:02
-	8679	getter\$3	USPAT; US-PGPUB	2003/06/02 17:03
-	44	kim.in. and getter\$3	USPAT; US-PGPUB	2003/06/02 17:03
-	16337	getter\$3 or getter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:50
-	2089	"semiconductor energy laboratory"	USPAT; US-PGPUB	2003/06/03 13:52
-	19706	tft or (thin adj film adj transistor)	USPAT; US-PGPUB	2003/06/03 13:58

-	641	(getter\$3 or getter) and (tft or (thin adj film adj transistor))	USPAT; US-PGPUB	2003/06/03 14:00
-	248	((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory"	USPAT; US-PGPUB	2003/06/03 14:00
-	40	((((getter\$3 or getter) and (tft or (thin adj film adj transistor)))) not "semiconductor energy laboratory") and @ad<20010216) and 438/\$.ccls.	USPAT; US-PGPUB	2003/06/03 14:02
-	111	((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<20010216	USPAT; US-PGPUB	2003/06/03 18:03
-	32627	ozone	USPAT; US-PGPUB	2003/06/03 18:02
-	110	((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<20010216	USPAT; US-PGPUB	2003/06/03 18:03
-	3	ozone and (((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<20010216)	USPAT; US-PGPUB	2003/06/03 18:12
-	66319	deioniz\$3	USPAT; US-PGPUB	2003/06/03 18:13
-	0	((((getter\$3 or getter) and (tft or (thin adj film adj transistor)))) not "semiconductor energy laboratory") and @ad<20010216) and deioniz\$3	USPAT; US-PGPUB	2003/06/03 18:13
-	556	((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.	USPAT; US-PGPUB	2003/06/06 12:37
-	18319	amorphous\$3 and crystal\$8 and laser	USPAT; US-PGPUB	2003/06/06 12:38
-	692277	barrier or (oxide or nitride or oxynitride)	USPAT; US-PGPUB	2003/06/06 12:38
-	61	((((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser))	USPAT; US-PGPUB	2003/06/06 12:38
-	57	((((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))	USPAT; US-PGPUB	2003/06/06 14:19
-	57	((((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))	USPAT; US-PGPUB	2003/06/06 14:22
-	5183	catalytic near metal	USPAT; US-PGPUB	2003/06/06 14:24
-	1	(((((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))) and (catalytic near metal)	USPAT; US-PGPUB	2003/06/06 14:21
-	112610	amorphous\$3	USPAT; US-PGPUB	2003/06/06 14:22
-	505011	crystal\$8	USPAT; US-PGPUB	2003/06/06 14:23
-	260315	laser	USPAT; US-PGPUB	2003/06/06 14:23
-	692277	barrier or (oxide or nitride or oxynitride)	USPAT; US-PGPUB	2004/04/13 09:13
-	28707	(catalytic or cluster or element) near metal	USPAT; US-PGPUB	2003/06/06 14:25
-	2556	crystal\$8 same ((catalytic or cluster or element) near metal)	USPAT; US-PGPUB	2003/06/06 14:25
-	1285	(crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3	USPAT; US-PGPUB	2003/06/06 14:25

-	709	((crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3) and laser	USPAT; US-PGPUB	2003/06/06 14:26
-	676	((crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3) and laser) and (barrier or (oxide or nitride or oxynitride))	USPAT; US-PGPUB	2003/06/06 14:26
-	8423	getter or gettering	USPAT; US-PGPUB	2003/06/06 14:26
-	233	(((((crystal\$8 same ((catalytic or cluster or element) near metal)) and amorphous\$3) and laser) and (barrier or (oxide or nitride or oxynitride))) and (getter or gettering)	USPAT; USPAT; US-PGPUB	2003/06/06 14:45
-	5636607	((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)	USPAT; US-PGPUB	2003/06/06 14:50
-	124463	((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8	USPAT; US-PGPUB	2003/06/06 14:51
-	29298	amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)	USPAT; US-PGPUB	2003/06/06 14:51
-	22525	(amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and (barrier or (oxide or nitride or oxynitride))	USPAT; US-PGPUB	2003/06/06 14:51
-	690	((amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and (barrier or (oxide or nitride or oxynitride))) and (getter or gettering)	USPAT; US-PGPUB	2003/06/06 14:52
-	531	((amorphous\$3 and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and (barrier or (oxide or nitride or oxynitride))) and (getter or gettering)) and laser	USPAT; US-PGPUB	2003/06/06 14:52
-	133656	(barrier or (oxide or nitride or oxynitride)) near (film or layer)	USPAT; US-PGPUB	2003/06/06 15:23
-	14785	((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)	USPAT; USPAT; US-PGPUB	2003/06/06 15:23
-	6367	((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or(co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and amorphous\$3	USPAT; US-PGPUB	2003/06/06 15:24

-	614	(((((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or (co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and amorphous\$3) and (getter or gettering)	USPAT; US-PGPUB	2003/06/06 15:24
-	511	(((((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or (co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and amorphous\$3) and (getter or gettering)) and laser	USPAT; US-PGPUB	2003/06/06 15:24
-	44	5821138.URPN.	USPAT	2003/06/06 15:49
-	5	("4838654" "5376561" "5488012" "5529937" "5618739").PN.	USPAT	2003/06/06 15:54
-	13	("4024626" "4759610" "4771016" "4838654" "4885616" "4906587" "4968638" "4980308" "4984033" "5110748" "5206749" "5256562" "5455187").PN.	USPAT	2003/06/06 15:54
-	13	("4024626" "4759610" "4771016" "4838654" "4885616" "4906587" "4968638" "4980308" "4984033" "5110748" "5206749" "5256562" "5455187").PN.	USPAT	2003/06/06 15:54
-	0	6337259.URPN.	USPAT	2003/06/06 16:14
-	1	"6140166".PN.	USPAT	2003/06/06 16:14
-	0	6337259.URPN.	USPAT	2003/06/06 16:15
-	0	6376336.URPN.	USPAT	2003/06/06 17:06
-	30	("3936858" "4498227" "5194395" "5244819" "5272104" "5443661" "5453153" "5501993" "5646053" "5753560" "5773152" "5795809" "5807771" "5818085" "5882990" "5899732" "5926727" "5929508" "5965917" "5976956" "6001711" "6010950" "6013584" "6022793" "6024888" "6083324" "6093624" "6100202" "6114223" "6133123").PN.	USPAT	2003/06/06 17:06
-	1	("5605847").PN.	USPAT; US-PGPUB	2003/06/15 11:57
-	1	("6097037").PN.	USPAT; US-PGPUB	2003/06/15 11:57
-	1	("6337259").PN.	USPAT; US-PGPUB	2003/06/15 12:10
-	36	funai.in.	USPAT; US-PGPUB	2003/06/15 16:13
-	1	("5550070").PN.	USPAT; US-PGPUB	2003/06/15 16:49
-	7255	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:20
-	9600	noble near gas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:17
-	260833	anneal or heat near2 treatment	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:18

-	12617	getter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:50
-	205	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and getter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:20
-	5	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and getter) and (noble near gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:19
-	1598	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (anneal or heat near2 treatment)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:21
-	66	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (noble near gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:33
-	56	(438/310).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:44
-	230662	helium or neon or argon or krypton or xenon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:05
-	1114	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (helium or neon or argon or krypton or xenon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:46
-	424	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (helium or neon or argon or krypton or xenon)) and (anneal or heat near2 treatment)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:46
-	30	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (helium or neon or argon or krypton or xenon)) and (anneal or heat near2 treatment)) and getter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:46
-	16843	getter or gettering	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:50
-	3575	(helium or neon or argon or krypton or xenon) and (getter or gettering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:51
-	1152	((helium or neon or argon or krypton or xenon) and (getter or gettering)) and (anneal or heat near2 treatment)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:51

-	711655	((metallic or(metal\$4 adj (cluster\$1 or element\$1))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:58
-	579	((((helium or neon or argon or krypton or xenon) and (getter or gettering)) and (anneal or heat near2 treatment)) and ((metallic or(metal\$4 adj (cluster\$1 or element\$1))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:59
-	1303417	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:59
-	464	((((helium or neon or argon or krypton or xenon) and (getter or gettering)) and (anneal or heat near2 treatment)) and ((metallic or(metal\$4 adj (cluster\$1 or element\$1)))) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 15:00
-	210593	amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 15:00
-	305	(((((helium or neon or argon or krypton or xenon) and (getter or gettering)) and (anneal or heat near2 treatment)) and ((metallic or(metal\$4 adj (cluster\$1 or element\$1)))) and semiconductor) and amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 15:36
-	5	("5696003").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 15:36
-	35	5696003.URPN.	USPAT	2003/11/20 15:37
-	17	("3783049" "4068020" "4309223" "5147826" "5275851" "5278093" "5289030" "5403772" "5481121" "5488000" "5501989" "5508533" "5529937" "5531182" "5534716" "5543352" "5569610").PN.	USPAT	2003/11/20 15:58
-	37	"5696003"	USPAT; US-PGPUB	2003/11/20 16:22
-	1	((("5696003").PN.) and (helium or neon or argon or krypton or xenon)	USPAT; US-PGPUB	2003/11/20 16:23
-	1	("5505070").PN.	USPAT; US-PGPUB	2003/11/20 16:48
-	1990466	(He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:13
-	51494	crystallize or crystallizing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:14
-	82959	polycrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:15
-	15068	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) and (crystallize or crystallizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:29

-	1413	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) and (crystallize or crystallizing)) and polycrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:15
-	14	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near (crystallize or crystallizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:29
-	139342	implant or implanting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:35
-	230817	(implant or implanting) or (dope or doping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:36
-	467	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near ((implant or implanting) or (dope or doping))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:36
-	2	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near ((implant or implanting) or (dope or doping))) same (crystallize or crystallizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:38
-	15	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near ((implant or implanting) or (dope or doping))) and (crystallize or crystallizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 12:38
-	1	("6391690").PN.	USPAT; US-PGPUB	2003/11/21 13:08
-	5986	getter	USPAT; US-PGPUB	2003/11/21 13:08
-	0	((("6391690").PN.) and getter	USPAT; US-PGPUB	2003/11/21 13:08
-	1	"6337259"	USPAT; US-PGPUB	2003/11/21 13:19
-	1	laser and "6337259"	USPAT; US-PGPUB	2003/11/21 13:19
-	1	("5696003").PN.	USPAT; US-PGPUB	2003/11/21 13:41
-	7538	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:12
-	783211	barrier or (oxide or nitride or oxynitride)	USPAT; US-PGPUB	2004/04/13 09:15
-	400286	(barrier or (oxide or nitride or oxynitride)) near2 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:16
-	147288	semiconductor near (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:16
-	17881	getter or gettering	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:16

-	29458	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:16
-	907	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:16
-	122	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:20
-	29458	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:20
-	2602	Semiconductor adj energy adj laboratory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:22
-	2542	(Semiconductor adj energy adj laboratory) not (((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:22
-	62	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering))) not (Semiconductor adj energy adj laboratory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:34
-	0	second near semiconductor near2 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:38
-	8543	second near semiconductor near2 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:38
-	1239	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:39
-	80	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))) and (getter or gettering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:39
-	43	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))) and (getter or gettering)) not (Semiconductor adj energy adj laboratory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:39

-	4	(((((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))) and (getter or gettering)) not (Semiconductor adj energy adj laboratory)) and (((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:40
-	4	Semiconductor adj energy adj laboratories	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 18:47
-	2600	Semiconductor adj energy adj laboratory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 18:51
-	17891	getter or gettering	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 18:51
-	571	(Semiconductor adj energy adj laboratory) and (getter or gettering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 18:51
-	191804	inert adj gas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 18:52
-	205	((Semiconductor adj energy adj laboratory) and (getter or gettering)) and (inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 18:52
-	204382	semiconductor near2 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 18:52
-	205	((Semiconductor adj energy adj laboratory) and (getter or gettering)) and (inert adj gas)) and (semiconductor near2 (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 19:05
-	97068	barrier near2 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 19:06
-	55	(((((Semiconductor adj energy adj laboratory) and (getter or gettering)) and (inert adj gas)) and (semiconductor near2 (film or layer))) and (barrier near2 (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 19:26
-	2	("6048758") or ("5248630")).PN.	USPAT	2004/04/19 15:05